

KSB834

Low Frequency Power Amplifier

• Complement to KSD880



1.Base 2.Collector 3.Emitter

PNP Silicon Epitaxial Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	- 60	V
V _{CEO}	Collector-Emitter Voltage	- 60	V
V_{EBO}	Emitter-Base Voltage	- 7	V
I _C	Collector Current	- 3	Α
I _B	Base Current	- 0.5	Α
P _C	Collector Dissipation (T _C =25°C)	30	W
P _C	Collector Dissipation (T _a =25°C)	1.5	W
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CBO}	Collector Cut-off Current	$V_{CB} = -60V, I_{E} = 0$			- 100	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -7V, I_{C} = 0$			- 100	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = -50 \text{mA}, I_B = 0$	- 60			V
h _{FE1}	DC Current Gain	$V_{CE} = -5V, I_{C} = -0.5A$ $V_{CE} = -5V, I_{C} = -3A$	60 20		200	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -3A, I_B = -0.3A$		- 0.5	- 1	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = -5V, I_{C} = -0.5A$		- 0.7	- 1	V
f _T	Current Gain Bandwidth Product	$V_{CE} = -5V, I_{C} = -0.5A$		9		MHz
C _{ob}	Output Capacitance	V _{CB} = - 10V, I _E = 0 f = 1MHz		150		pF
t _{ON}	Turn ON Time	$V_{CC} = -30V, I_{C} = -1A$		0.4		μs
T _{STG}	Storage Time	$I_{B1} = -I_{B2} = -0.2A$		1.7		μs
t _F	Fall Time	$R_L = 30\Omega$		0.5		μs

h_{FE} Classification

Classification	0	Υ
h _{FE1}	60 ~ 120	100 ~ 200

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Typical Characteristics

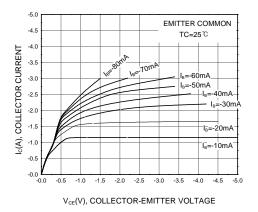


Figure 1. Static Characteristic

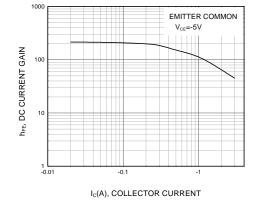


Figure 2. DC current Gain

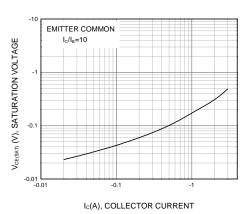


Figure 3. Collector-Emitter Saturation Voltage

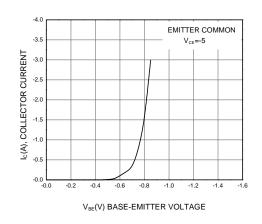


Figure 4. Base-Emitter On Voltage

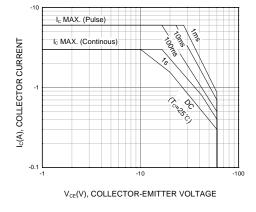


Figure 5. Safe Operating Area

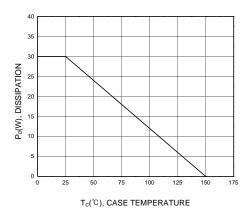
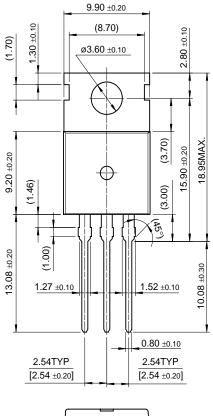


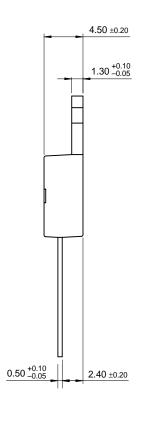
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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